

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: 2SC3324GRTE85LF
Manufacturer: Toshiba Semiconductor and Storage
Package: TO-236-3, SC-59, SOT-23-3
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/toshiba-semiconductor-and-storage-2sc3324grte85lf.html>

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

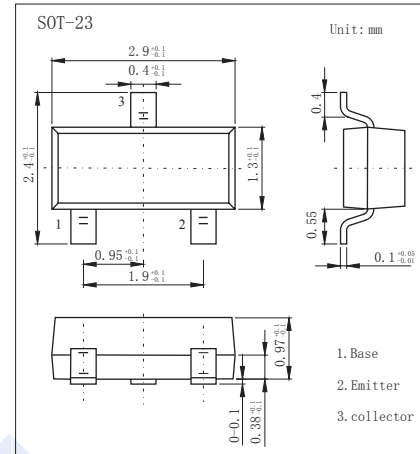
The original manufacturer datasheet follows from the next page.

NPN Transistors

2SC3324

■ Features

- Collector Current Capability $I_C=100\text{mA}$
- Collector Emitter Voltage $V_{CEO}=120\text{V}$
- Complementary to 2SA1312

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	120	V
Collector - Emitter Voltage	V_{CEO}	120	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	100	mA
Base Current	I_B	20	
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100\ \mu\text{A}, I_E = 0$	120			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1\ \text{mA}, I_B = 0$	120			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100\ \mu\text{A}, I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 120\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\ \text{mA}, I_B = 1\ \text{mA}$			0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\ \text{mA}, I_B = 1\ \text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}, I_C = 2\ \text{mA}$	200		700	
Noise figure	NF	$V_{CE} = 6\text{V}, I_C = 0.1\ \text{mA}, f = 100\text{Hz}, R_G = 10\text{K}\Omega$			6	dB
		$V_{CE} = 6\text{V}, I_C = 0.1\ \text{mA}, f = 1\ \text{kHz}, R_G = 10\text{K}\Omega$			3	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		4		pF
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_C = 1\ \text{mA}$		100		MHz

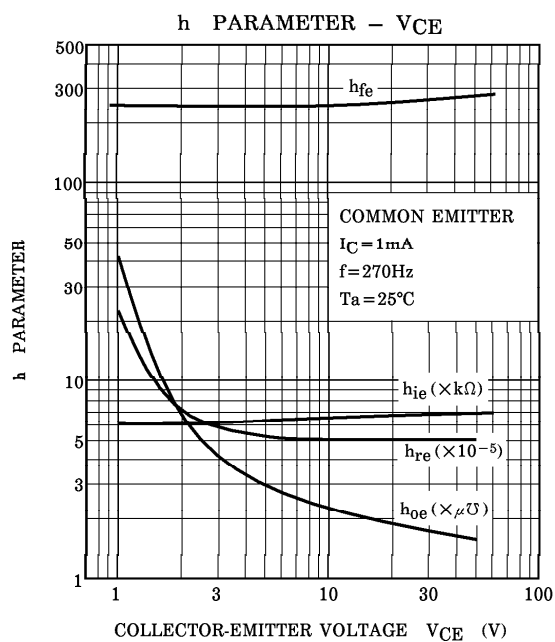
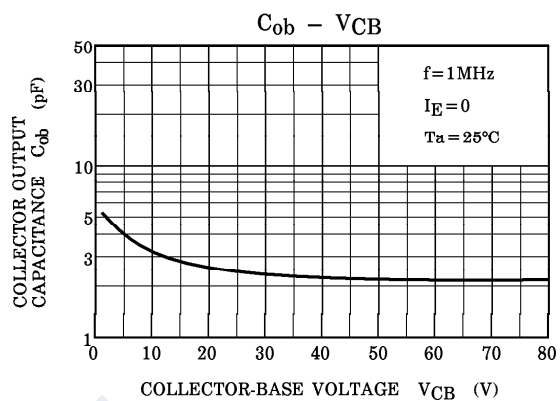
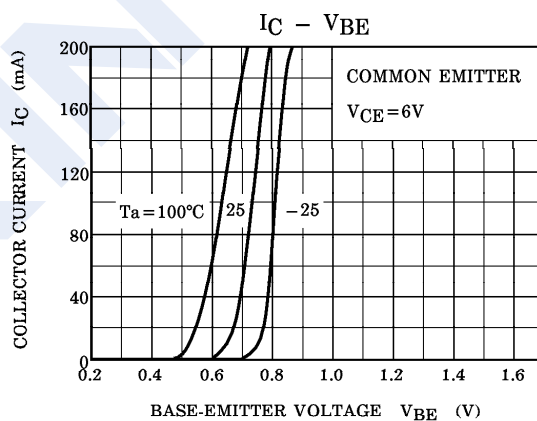
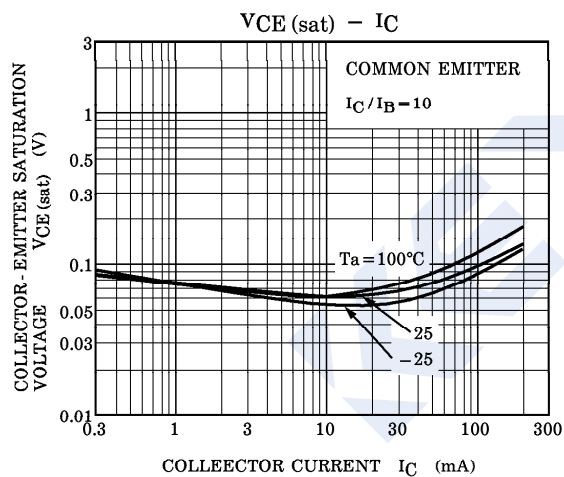
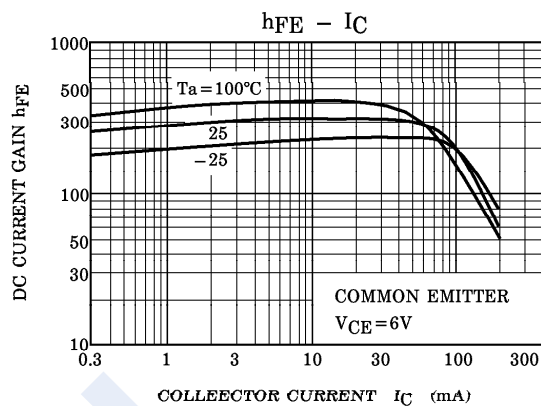
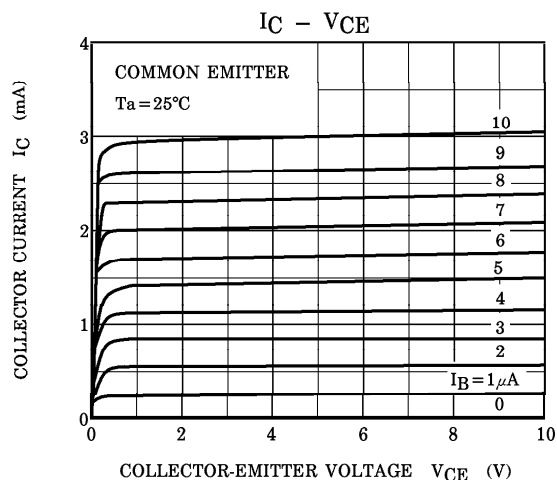
■ Classification of h_{FE}

Type	2SC3324-G	2SC3324-L
Range	200-400	350-700
Marking	CB G	CB L

NPN Transistors

2SC3324

■ Typical Characteristics



NPN Transistors

2SC3324

■ Typical Characteristics

